

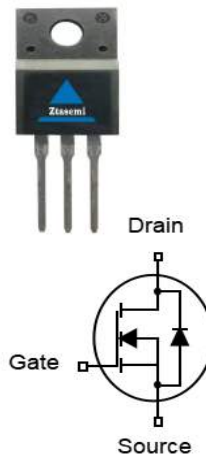
Features

- N-Channel
- Low $R_{DS(on)}$
- Low gate charge (typ. $Q_g = 41.9$ nC)
- 100% UIS tested
- RoHS compliant
- 100% EAS Tested

V_{DS}	650	V
$R_{DS(on),TYP}@ V_{GS}=10$ V	640	m Ω
I_D	12	A



Part ID	Package Type	Marking	Packing
ZT12N65F	TO-220F	ZT12N65F	1000pcs/Tape

TO-220F


Absolute Maximum Ratings $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit	
Common Ratings ($T_c=25^\circ\text{C}$ Unless Otherwise Noted)				
V_{GS}	Gate-Source Voltage	± 30	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	650	V	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
I_{DM}	Drain Current-Continuous@ Current-Pulsed (Note 1)	$T_c = 25^\circ\text{C}$ 48	A	
Mounted on Large Heat Sink				
I_D	Drain Current-Continuous	$T_c = 25^\circ\text{C}$	12	A
		$T_c = 100^\circ\text{C}$	7.5	A
P_D	Maximum Power Dissipation		42	W
		Derate above 25°C	0.34	W/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance-Junction to Case	2.98	$^\circ\text{C}/\text{W}$	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	110	$^\circ\text{C}/\text{W}$	
Drain-Source Avalanche Ratings				
EAS	Avalanche Energy, Single Pulsed (Note 2)	500	mJ	
dv/dt	Reverse Diode dv/dt (Note 3)	5	V/ns	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J=25°C (unless otherwise stated)						
V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	650	--	--	V
IDSS	Zero Gate Voltage Drain Current	V _{DS} =650V, V _{GS} =0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	V _{GS} =±30V, V _{DS} =0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2.0	--	4.0	V
RDS(on)	Drain-Source On-State Resistance	V _{GS} =10V, I _D =6A	--	640	800	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
Ciss	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	--	1998	--	pF
Coss	Output Capacitance		--	162	--	pF
Crss	Reverse Transfer Capacitance		--	7.3	--	pF
Qg	Total Gate Charge	V _{DD} =520V, I _D =12A, V _{GS} =0 to 10V	--	41.9	--	nC
Qgs	Gate-Source Charge		--	10.8	--	nC
Qgd	Gate-Drain Charge		--	15	--	nC
Vplateau	Gate plateau voltage		--	5	--	V
Switching Characteristics (Note 2)						
Td(on)	Turn-on Delay Time	V _{DD} =325V, I _D =12A, R _G =10Ω, V _{GS} =15V	--	14.5	--	ns
Tr	Turn-on Rise Time		--	37.6	--	ns
Td(off)	Turn-Off Delay Time		--	69	--	ns
Tf	Turn-Off Fall Time		--	16	--	ns
Source- Drain Diode Characteristics @ T_J = 25°C (unless otherwise stated)						
VSD	Forward on voltage	I _F =12A, V _{GS} =0V	--	--	1.5	V
Trr	Reverse Recovery Time	T _J =25°C, I _F =12A, V _R =325V di/dt=100A/μs	--	450.4	--	ns
Qrr	Reverse Recovery Charge		--	4.75	--	nC
Irrm	Peak Reverse Recovery Current		--	21.1	--	A

Notes:

- Pulse width limited by maximum junction temperature.
- L=10mH, I_{AS} = 10A, Starting T_J= 25°C.
- I_{SD} = 12A, di/dt ≤ 100A/μs, V_{DD} ≤ BV_{DS}, Starting T_J= 25°C.

Electrical Characteristics Diagrams

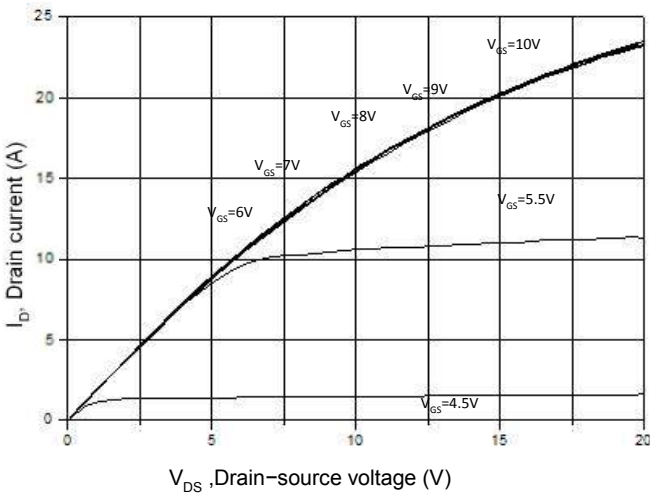


Figure 1. Typical Output Characteristics

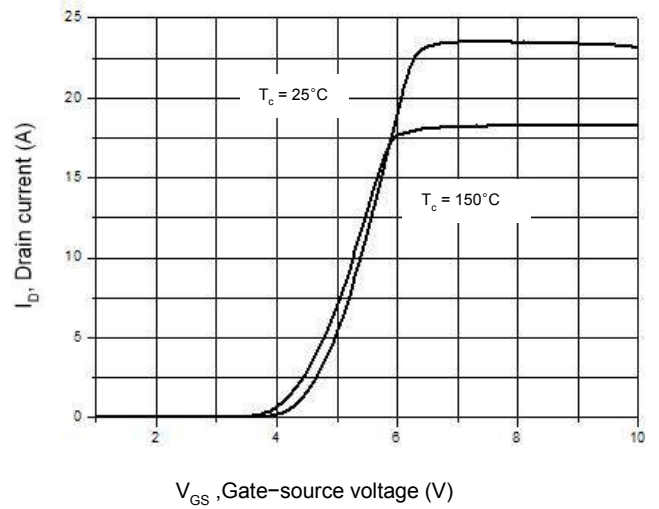


Figure 2. Transfer Characteristics

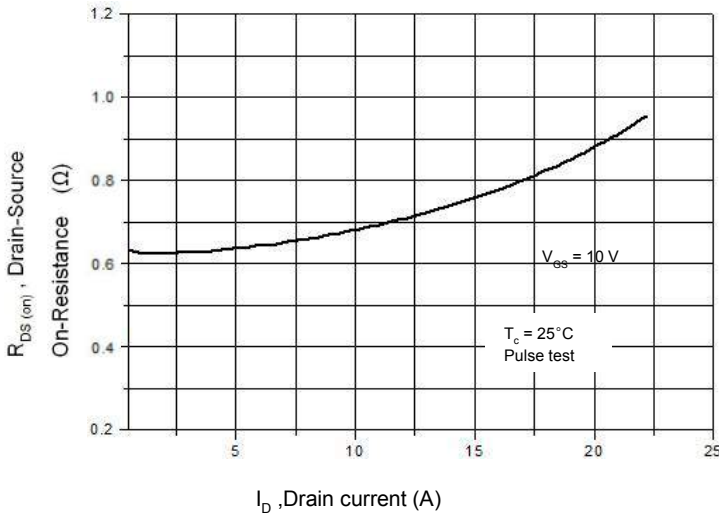


Figure 3. On-Resistance Variation vs. Drain Current

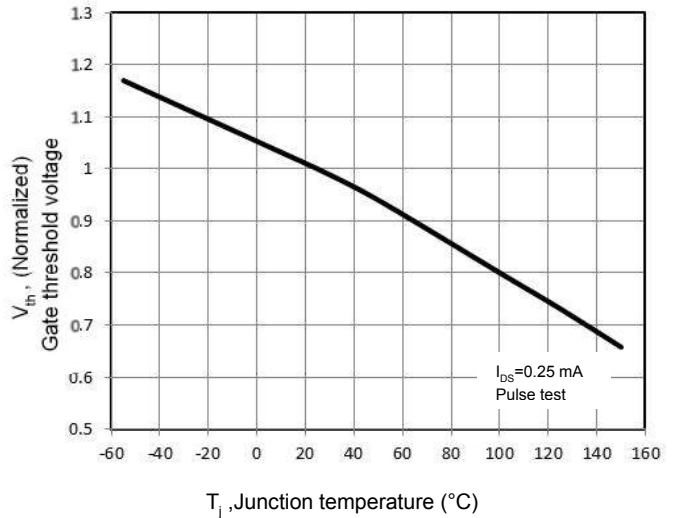


Figure 4. Threshold Voltage vs. Temperature

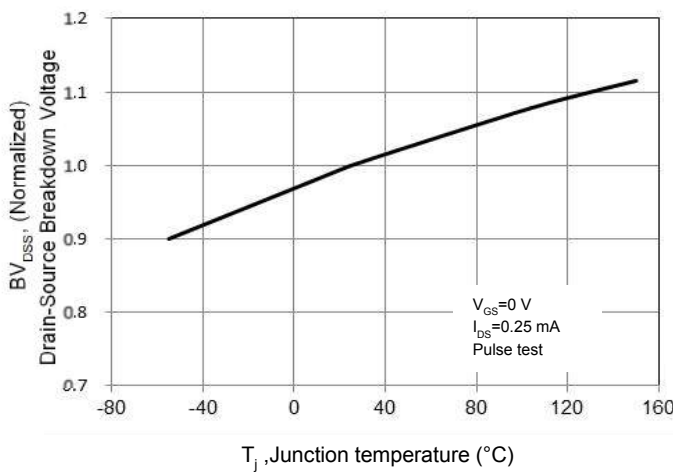


Figure 5. Breakdown Voltage vs. Temperature

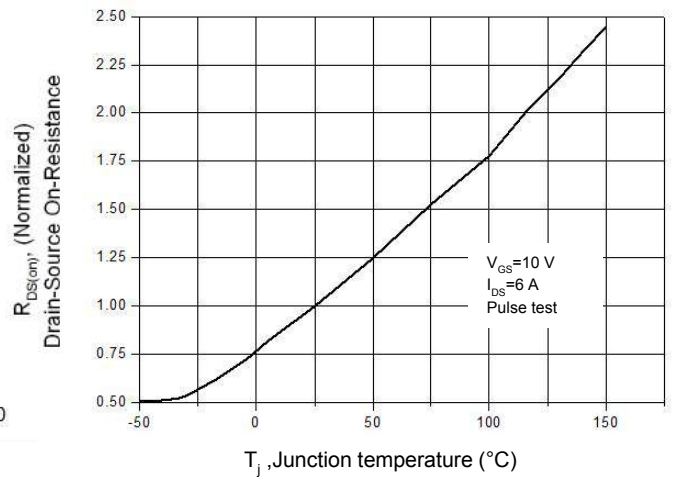


Figure 6. On-Resistance vs. Temperature

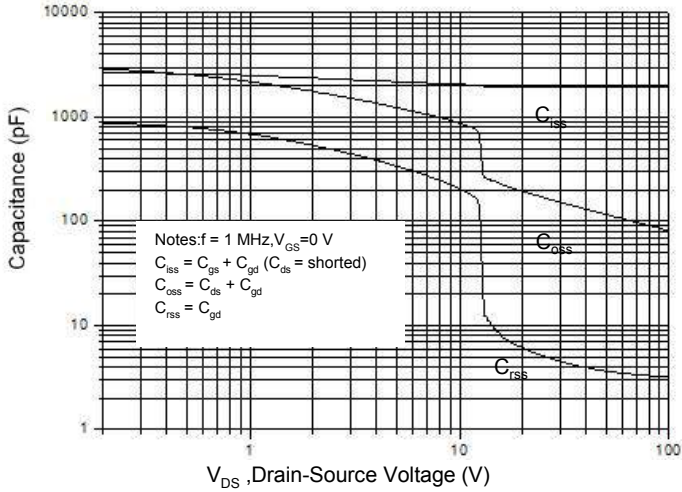


Figure 7. Capacitance Characteristics

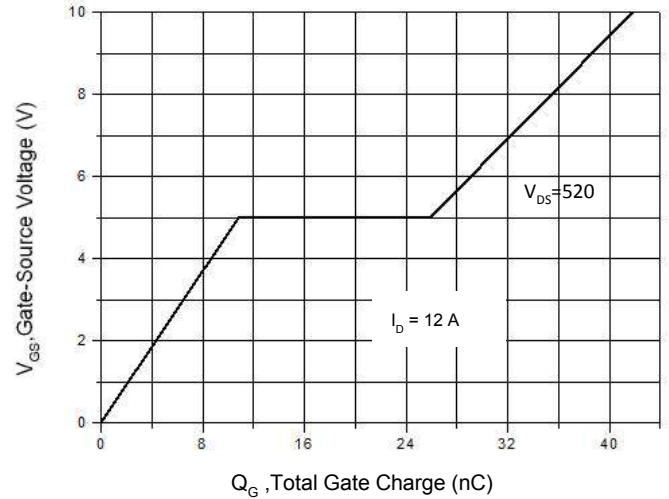


Figure 8. Gate Charge Characteristics

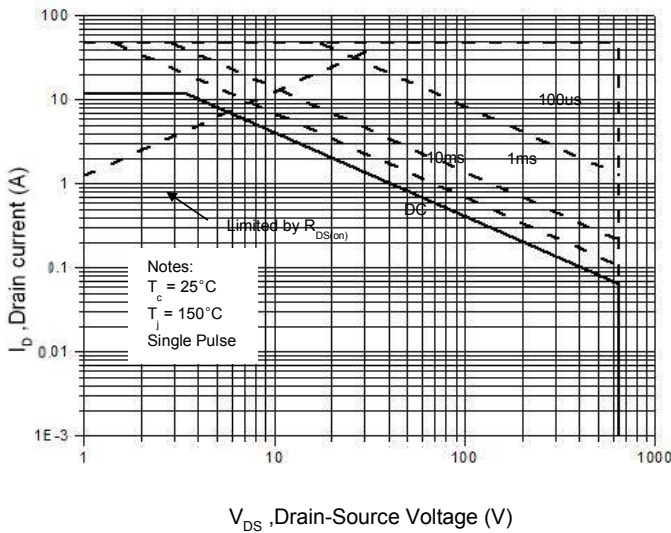


Figure 9. Maximum Safe Operating Area

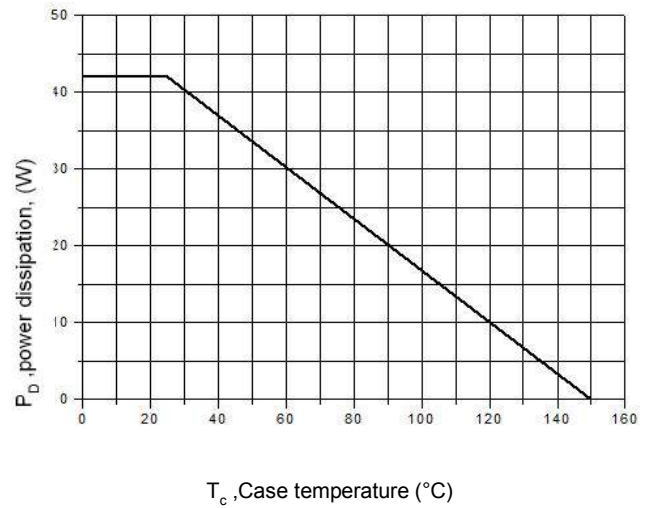


Figure 10. Power Dissipation vs. Temperature

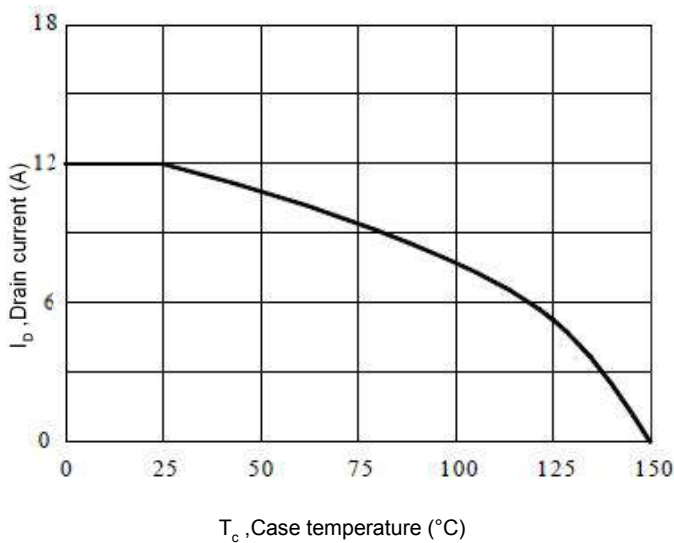


Figure 11. Continuous Drain Current vs. Temperature

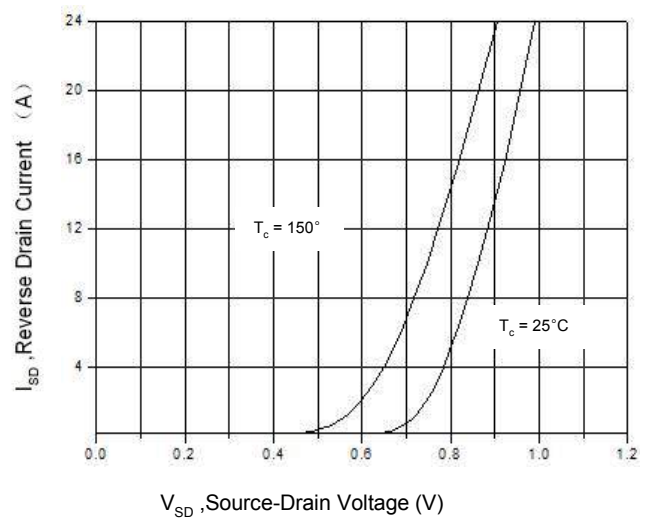


Figure 12. Body Diode Transfer Characteristics

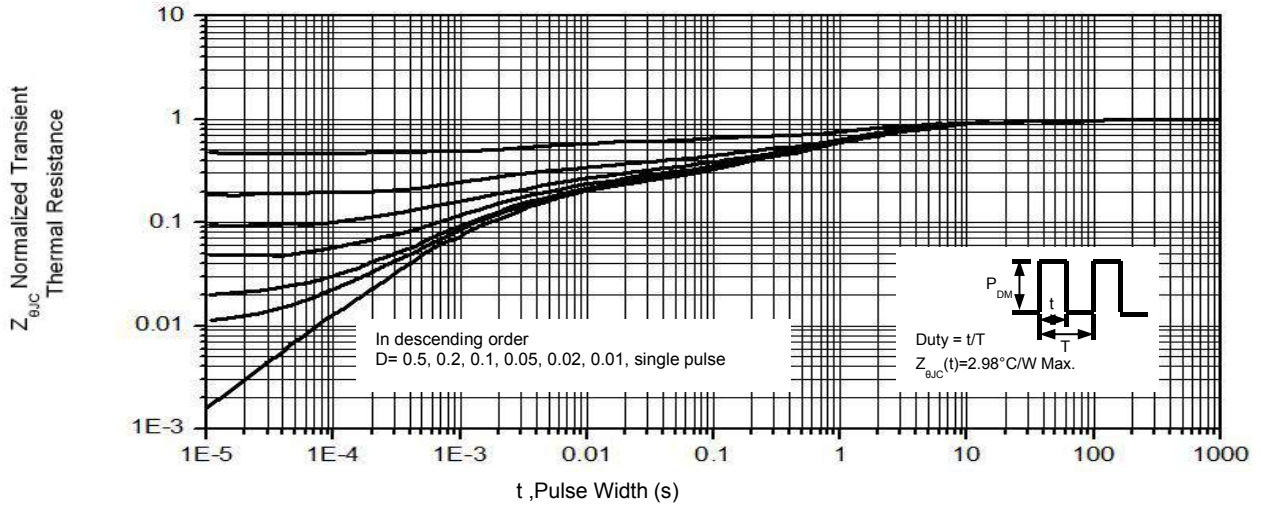
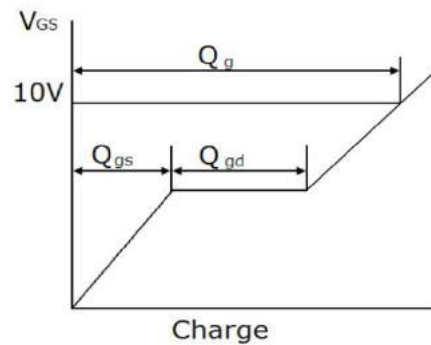
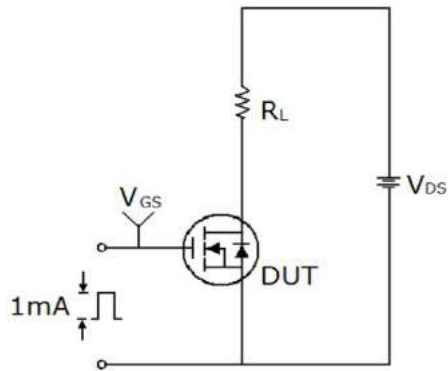
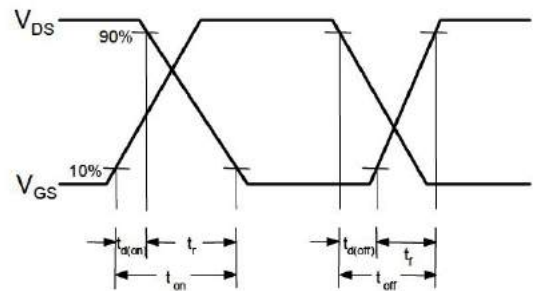
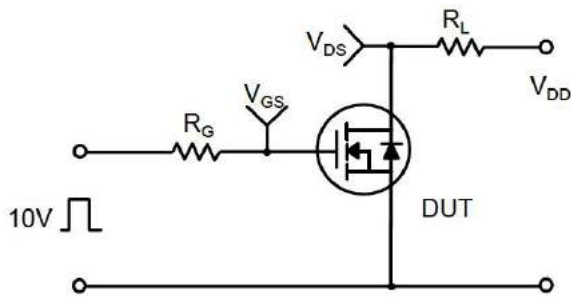


Figure 13 Transient Thermal Impedance, Junction to Case

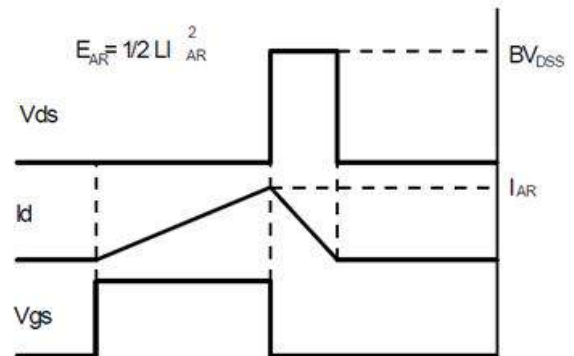
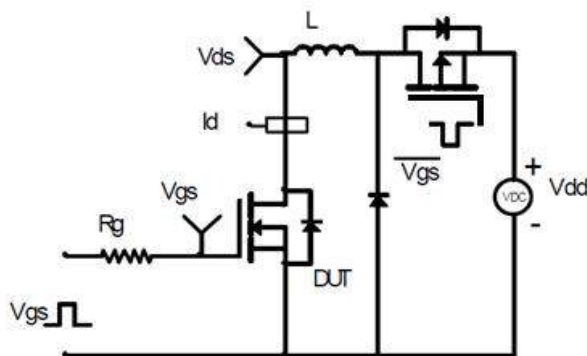
Gate Charge Test Circuit & Waveform



Switching Test Circuit & Waveforms

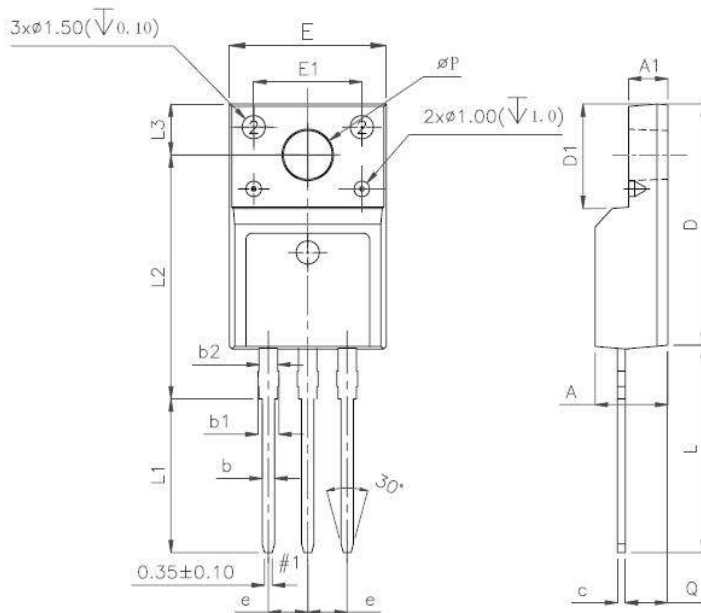


Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions for TO-220F

UNIT: mm



SYMBOL	MIN	NOM	MAX
A	4.5		4.9
A1	2.3		2.9
b	0.65		0.9
b1	1.1		1.7
b2	1.2		1.4
c	0.35		0.65
D	14.5		16.5
D1	6.1		6.9
E	9.6		10.3
E1	6.5	7	7.5
e	2.44	2.54	2.64
L	12.5		14.3
L1	9.45		10.05
L2	15		16
L3	3.2		4.4
ϕP	3		3.3
Q	2.5		2.9

Customer Service

Sales and Service:

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